Abstracts

Ka-Band 1 Watt Power GaAs MMICs (1988 Vol. I [MWSYM])

Y. Oda, S. Arai, T. Yoshida, H. Nakamura, S. Yanagawa, S. Hori and K. Kamei. "Ka-Band 1 Watt Power GaAs MMICs (1988 Vol. I [MWSYM])." 1988 MTT-S International Microwave Symposium Digest 88.1 (1988 Vol. I [MWSYM]): 413-416.

High-power and high-gain Ka-band GaAs MMICs have been developed using a Be co-implantation technique. At 29.5 GHz, an output power of 1 W with 4.2 dB gain has been obtained with gate width of 4.8 mm MMIC. This power gain is the highest value reported to date on Ka-band FETs providing an output power of 1 W. The intercept point of +42 dBm has been obtained from the 3rd order intermodulation distortion measurements.

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